



SEMiX® 4s

Trench IGBT Modules

SEMiX904GB126HDs

Features

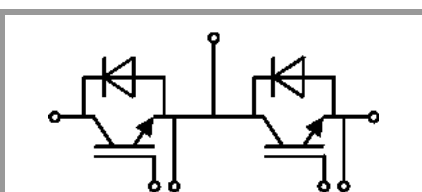
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to $T_C=125^\circ\text{C}$ max.
- Not for new design



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Absolute Maximum Ratings

Symbol	Conditions	Values	Unit
IGBT			
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V
I_C	$T_j = 150^\circ\text{C}$	$T_c = 25^\circ\text{C}$	821
		$T_c = 80^\circ\text{C}$	572
I_{Cnom}		600	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	1200	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 600\text{ V}$ $V_{GE} \leq 20\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 125^\circ\text{C}$	10
T_j		-40 ... 150	$^\circ\text{C}$
Inverse diode			
I_F	$T_j = 150^\circ\text{C}$	$T_c = 25^\circ\text{C}$	752
		$T_c = 80^\circ\text{C}$	516
I_{Fnom}		600	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	1200	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	3600	A
T_j		-40 ... 150	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	600	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50Hz, $t = 1\text{ min}$	4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 600\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.7	2.10	V
		$T_j = 125^\circ\text{C}$	2.0	2.45	V
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$	1	1.2	V
		$T_j = 125^\circ\text{C}$	0.9	1.1	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.2	1.5	m Ω
		$T_j = 125^\circ\text{C}$	1.8	2.3	m Ω
$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C = 24\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$		5	mA
		$T_j = 125^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	43.1		nF
C_{oes}		$f = 1\text{ MHz}$	2.25		nF
C_{res}		$f = 1\text{ MHz}$	1.95		nF
Q_G	$V_{GE} = -8\text{ V...} + 15\text{ V}$		4800		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		1.25		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 125^\circ\text{C}$	440		ns
t_r	$I_C = 600\text{ A}$ $V_{GE} = \pm 15\text{ V}$	$T_j = 125^\circ\text{C}$	85		ns
		$T_j = 125^\circ\text{C}$	60		mJ
E_{on}	$R_{G on} = 1.6\text{ }\Omega$	$T_j = 125^\circ\text{C}$	710		ns
$t_{d(off)}$	$R_{G off} = 1.6\text{ }\Omega$	$T_j = 125^\circ\text{C}$	130		ns
t_f		$T_j = 125^\circ\text{C}$	88		mJ
E_{off}		$T_j = 125^\circ\text{C}$			
$R_{th(j-c)}$	per IGBT			0.05	K/W

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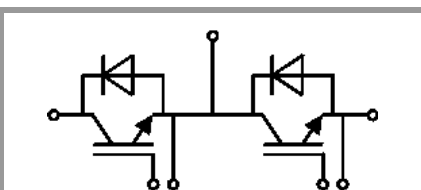
Typical Applications*

- AC inverter drives
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Remarks

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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 600 A	T _j = 25 °C		1.6	1.80	V
	V _{GE} = 0 V chiplevel	T _j = 125 °C		1.6	1.8	V
V _{F0}	chiplevel	T _j = 25 °C	0.9	1	1.1	V
		T _j = 125 °C	0.7	0.8	0.9	V
r _F	chiplevel	T _j = 25 °C	0.8	1.0	1.2	mΩ
		T _j = 125 °C	1.2	1.3	1.5	mΩ
I _{RRM}	I _F = 600 A	T _j = 125 °C		625		A
Q _{rr}	di/dt _{off} = 8400 A/μs	T _j = 125 °C		165		μC
E _{rr}	V _{GE} = -15 V	T _j = 125 °C		75		mJ
	V _{CC} = 600 V					
R _{th(j-c)}	per diode				0.081	K/W
Module						
L _{CE}				22		nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C		0.7		mΩ
		T _C = 125 °C		1		mΩ
R _{th(c-s)}	per module			0.03		K/W
M _s	to heat sink (M5)		3		5	Nm
M _t		to terminals (M6)	2.5		5	Nm
						Nm
w					400	g
Temperature Sensor						
R ₁₀₀	T _C =100°C (R ₂₅ =5 kΩ)			493 ± 5%		Ω
B _{100/125}	R(T)=R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];			3550 ±2%		K



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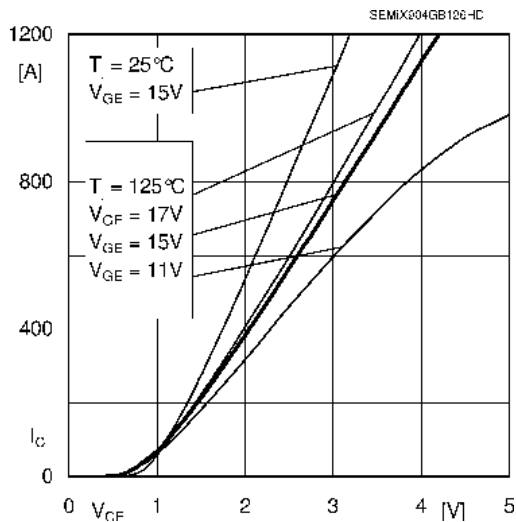


Fig. 1: Typ. output characteristic, inclusive $R_{CC'} + E_{E'}$

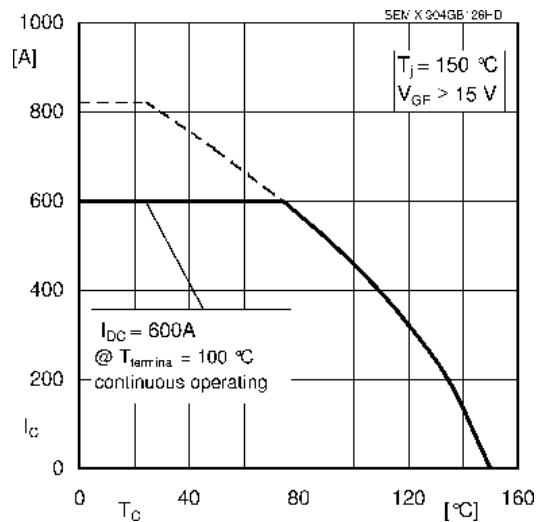


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

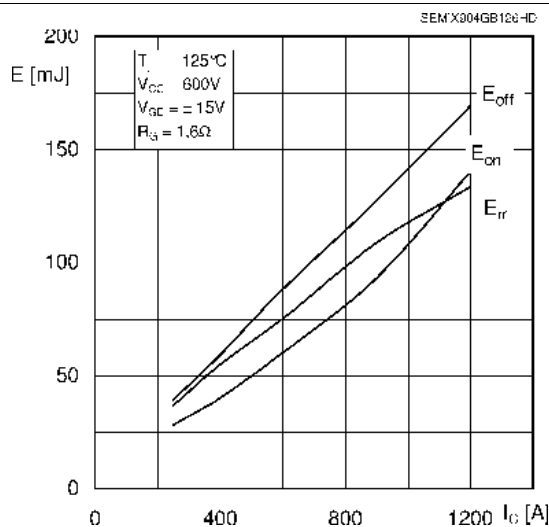


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

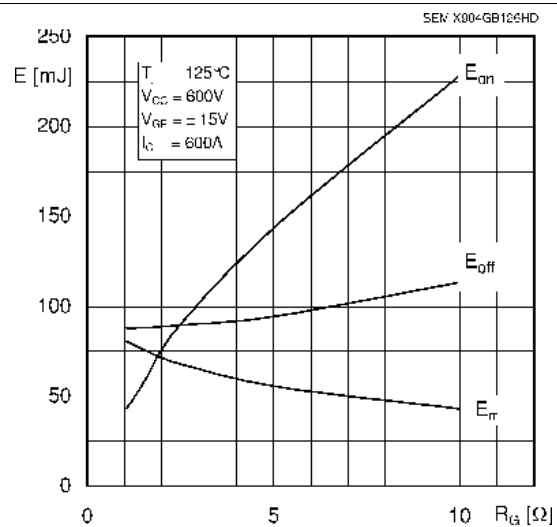


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

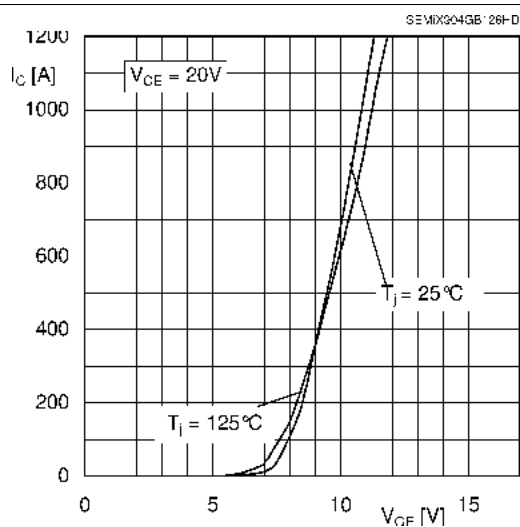


Fig. 5: Typ. transfer characteristic

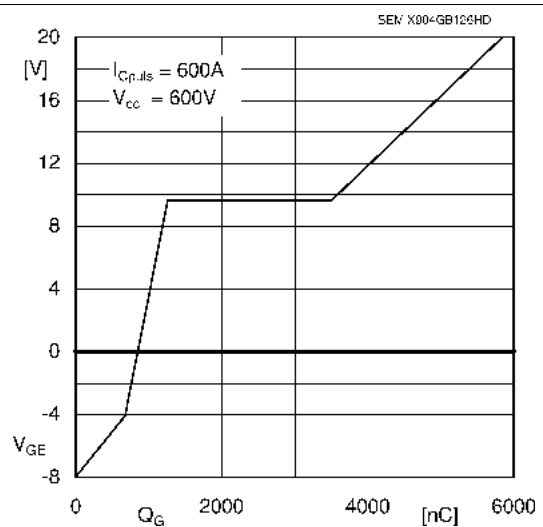


Fig. 6: Typ. gate charge characteristic

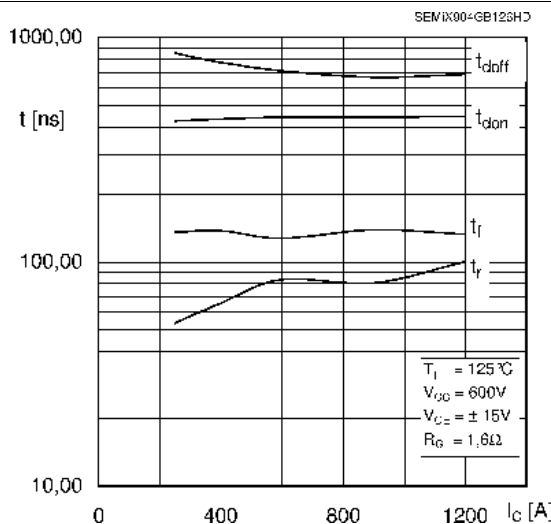


Fig. 7: Typ. switching times vs. I_C

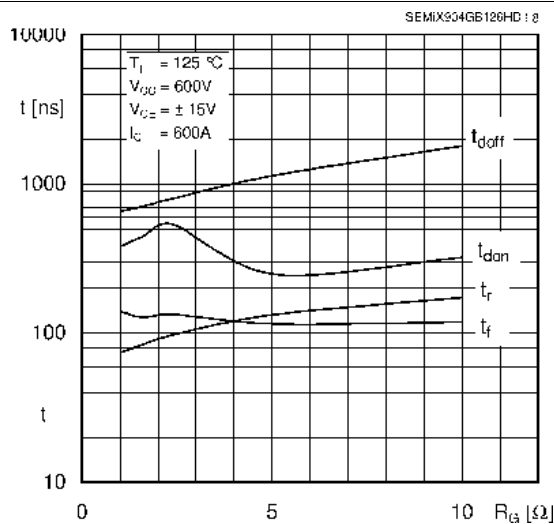


Fig. 8: Typ. switching times vs. gate resistor R_G

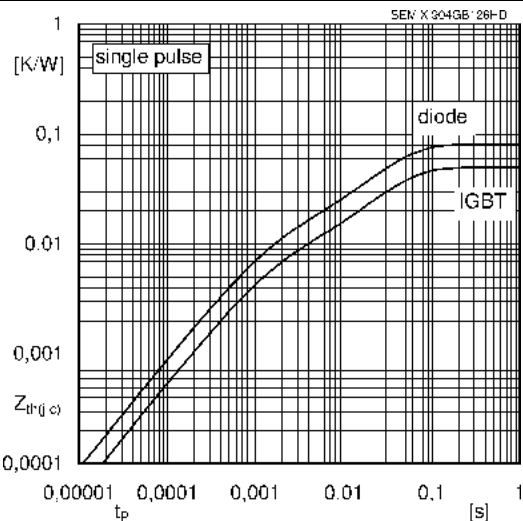


Fig. 9: Typ. transient thermal impedance

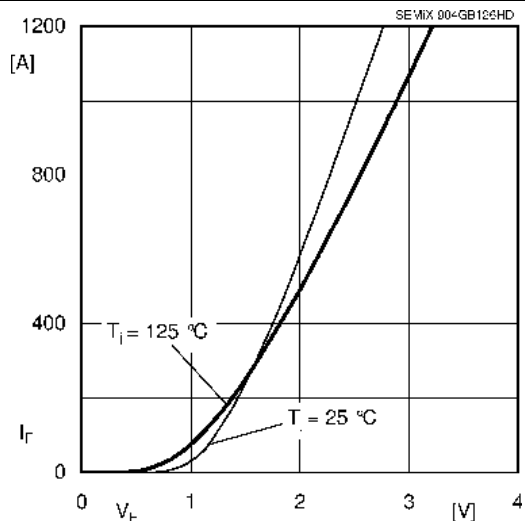


Fig. 10: Typ. CAL diode forward charact., incl. $R_{GG'+EE'}$

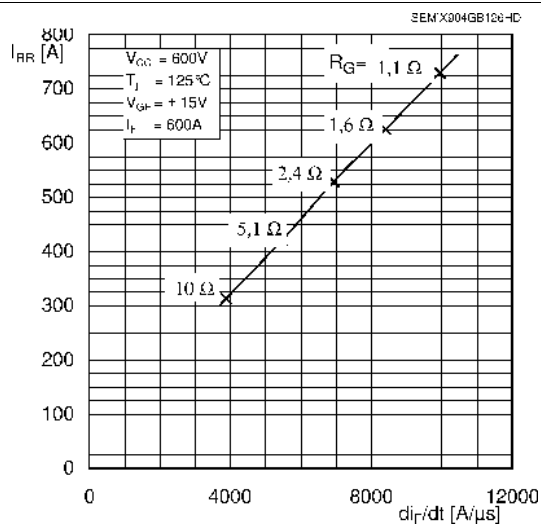


Fig. 11: Typ. CAL diode peak reverse recovery current

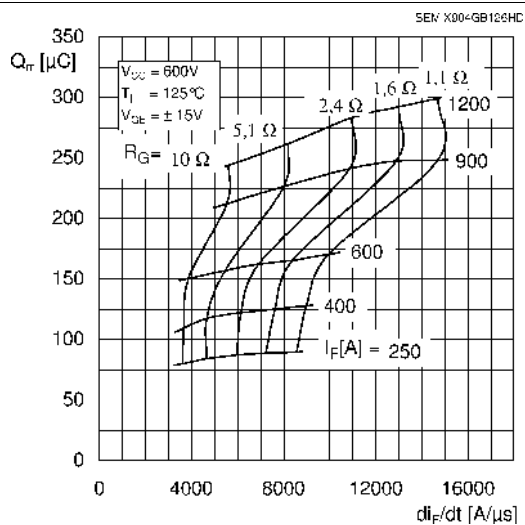
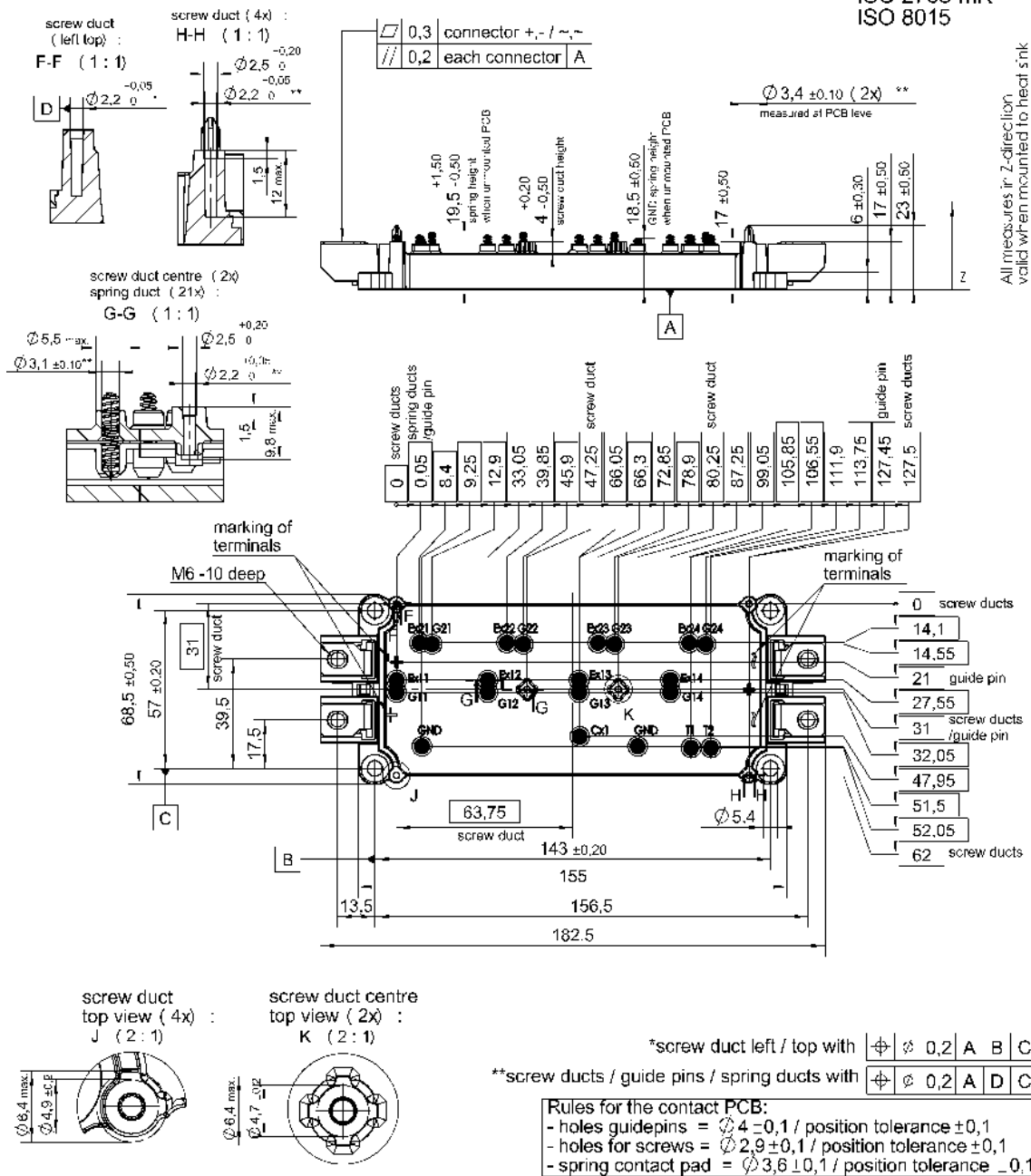


Fig. 12: Typ. CAL diode recovery charge

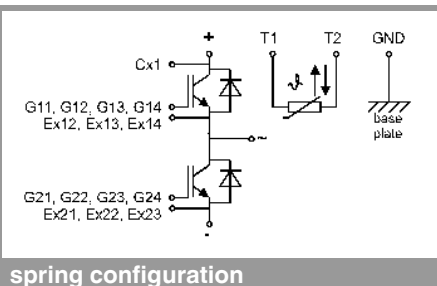
Case: SEMiX 4s

general tolerance:
ISO 2768-mK
ISO 8015



All measures in Z-direction valid when mounted to heat sink

SEMiX 4s



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.